



SEMIPACK® 0

Antiparallel Thyristor Module

SKKQ 31

Preliminary Data

Features

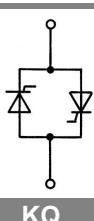
- Compact Design
- Heat transfer through aluminium oxide ceramic isolated metal baseplat
- UL recognized, file no. E 63 532

Typical Applications

- AC motor starters
- Light control (studios, theaters...)
- Temperature control

V_{RSM}	V_{RRM}, V_{DRM}	$I_{RMS} = 24 \text{ A}^1; 45 \text{ A}^2 \text{ A}$ (full conduction) ($T_s = 85^\circ\text{C}$)
700	600	SKKQ 45/06 E
900	800	SKKQ 45/08 E
1300	1200	SKKQ 45/12 E
1500	1400	SKKQ 45/14 E
1700	1600	SKKQ 45/16 E

Symbol	Conditions	Values	Units
I_{RMS}	$W1C ; \sin. 180^\circ ; T_{case} = 85^\circ\text{C}^{(2)}$ $; \sin. 180^\circ$	45	A
$I_{t RMS}$	$W1C, \sin. 180^\circ, T_{case}=85^\circ\text{C}$	32	A
I_{TSM}	$T_{vj} = 25^\circ\text{C} ; 10 \text{ ms}$ $T_{vj} = 125^\circ\text{C} ; 10 \text{ ms}$	470	A
i^2t	$T_{vj} = 25^\circ\text{C} ; 8,3\dots10 \text{ ms}$ $T_{vj} = 125^\circ\text{C} ; 8,3\dots10 \text{ ms}$	400 1100 800	A ² s
V_T	$T_{vj} = 25^\circ\text{C}, I_T = 75 \text{ A}$	max. 1,8	V
$V_{T(TO)}$	$T_{vj} = 125^\circ\text{C}$	max. 0,9	V
r_T	$T_{vj} = 125^\circ\text{C}$	max. 12	mΩ
$I_{DD}; I_{RD}$	$T_{vj} = 25^\circ\text{C}, V_{RD}=V_{RRM}$ $T_{vj} = 125^\circ\text{C}, V_{RD}=V_{RRM}$	max. 10	mA
t_{gd}	$T_{vj} = 25^\circ\text{C}, I_G = 1 \text{ A}; di_G/dt= 1 \text{ A}/\mu\text{s}$	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	1	μs
$(dv/dt)_{cr}$	$T_{vj} = 125^\circ\text{C}$	1000	V/μs
$(di/dt)_{cr}$	$T_{vj} = 125^\circ\text{C}; f= 50\dots60 \text{ Hz}$	100	A/μs
t_q	$T_{vj} = 125^\circ\text{C}; \text{typ.}$	80	μs
I_H	$T_{vj} = 25^\circ\text{C}; \text{typ. / max.}$	100 / 200	mA
I_L	$T_{vj} = 25^\circ\text{C}; R_G = 33 \Omega; \text{typ. / max.}$	250 / 400	mA
V_{GT}	$T_{vj} = 25^\circ\text{C}; \text{d.c.}$	min. 3	V
I_{GT}	$T_{vj} = 25^\circ\text{C}; \text{d.c.}$	min. 150	mA
V_{GD}	$T_{vj} = 125^\circ\text{C}; \text{d.c.}$	max. 0,25	V
I_{GD}	$T_{vj} = 125^\circ\text{C}; \text{d.c.}$	max. 5	mA
$R_{th(j-s)}$	cont. per thyristor sin 180° per thyristor	1,2 1,3	K/W
$R_{th(j-s)}$	cont. per W1C sin 180° per W1C	0,6 0,6	K/W
T_{vj}		-40 ... +125	°C
T_{stg}		-40 ... +125	°C
	terminals, 10s		°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	Mounting torque to heatsink	1,5	Nm
M_t		50	Nm
a			m/s ²
m			g
Case	SEMIPACK® 0	A 41	



SKKQ 45

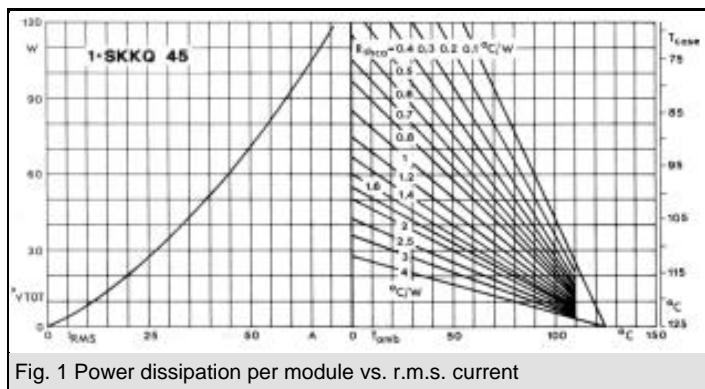


Fig. 1 Power dissipation per module vs. r.m.s. current

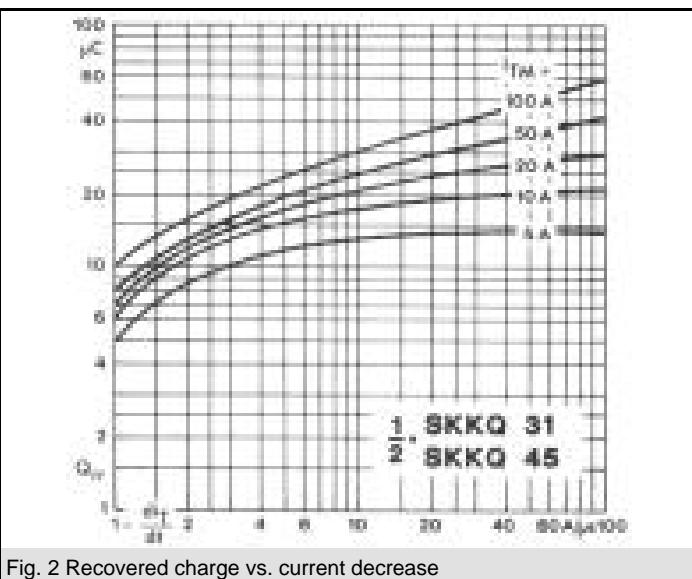


Fig. 2 Recovered charge vs. current decrease

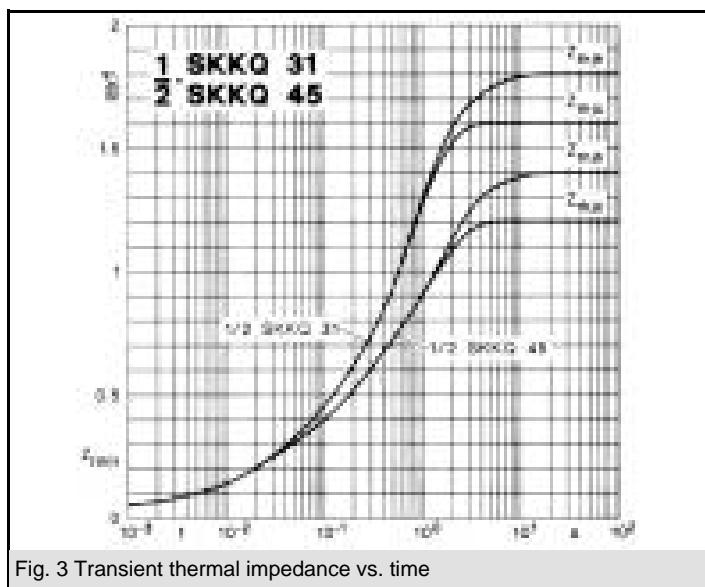


Fig. 3 Transient thermal impedance vs. time

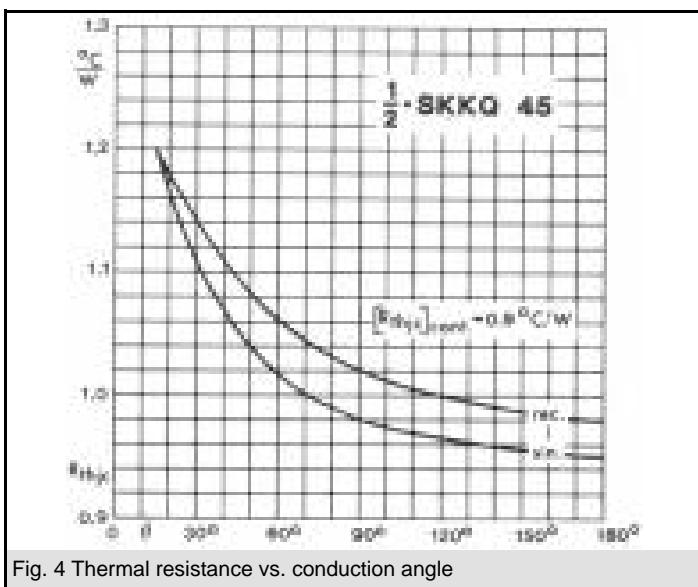


Fig. 4 Thermal resistance vs. conduction angle

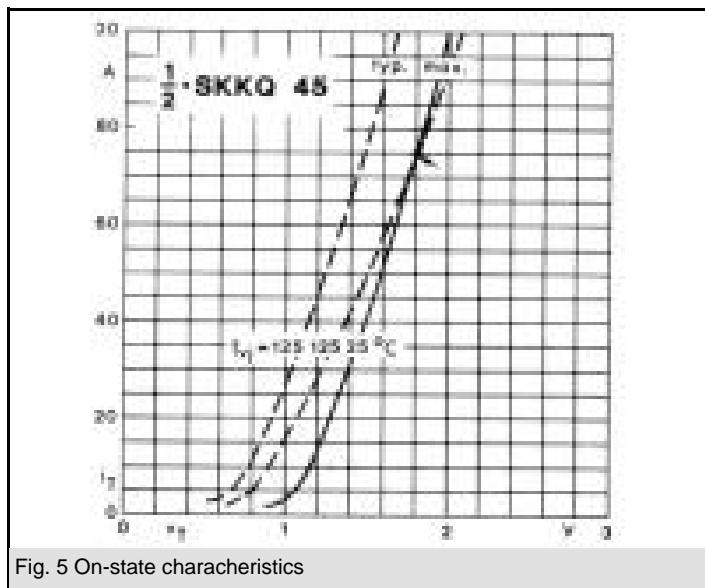


Fig. 5 On-state characteristics

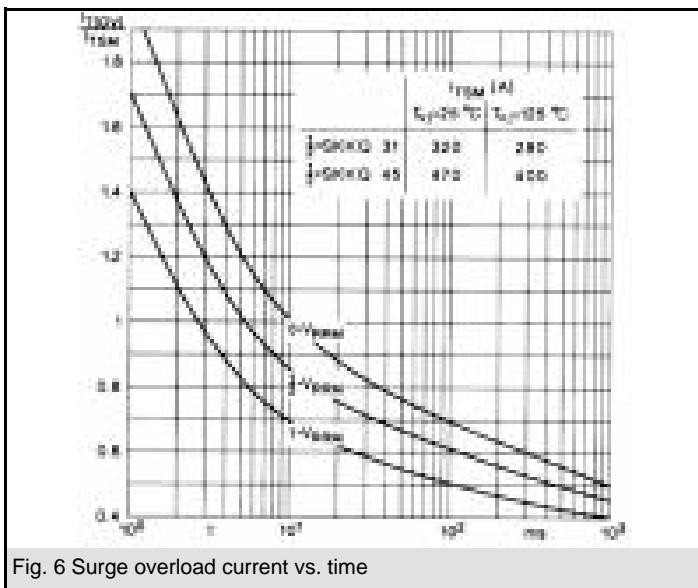


Fig. 6 Surge overload current vs. time

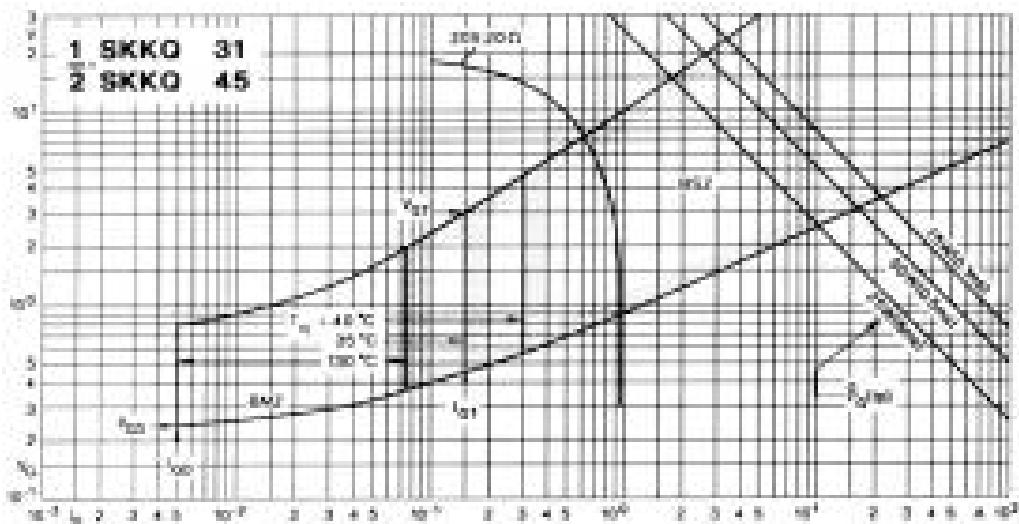
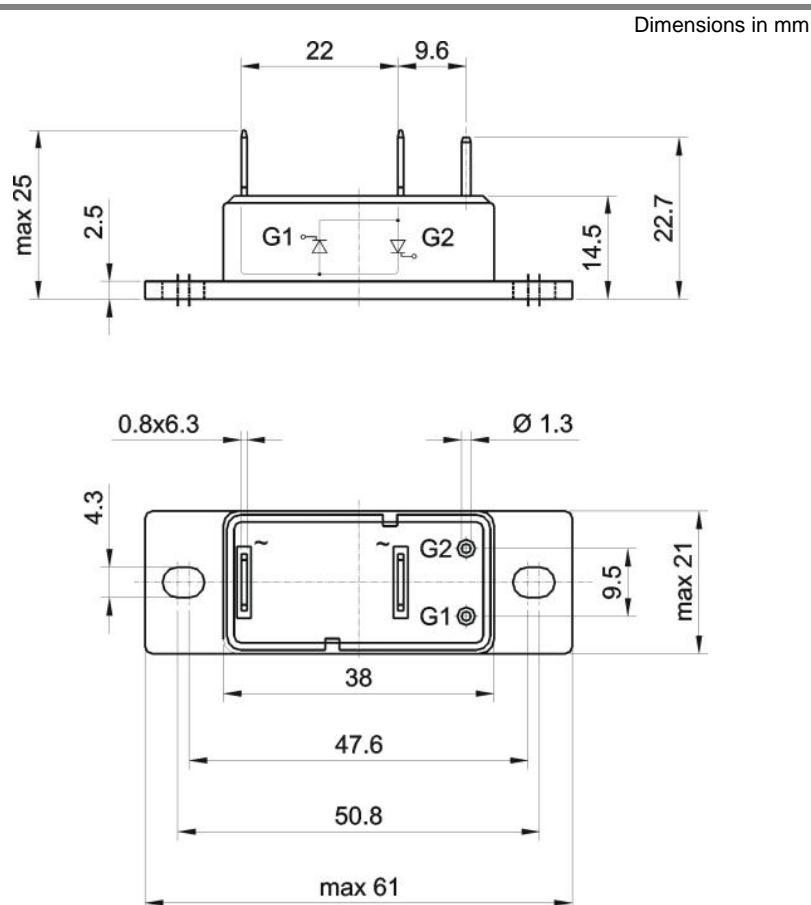


Fig. 5 Gate trigger characteristics



Case A41

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